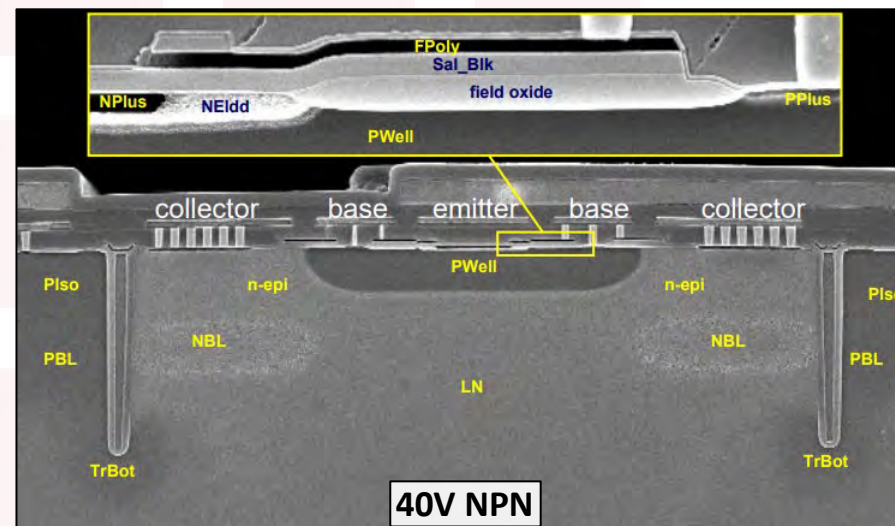
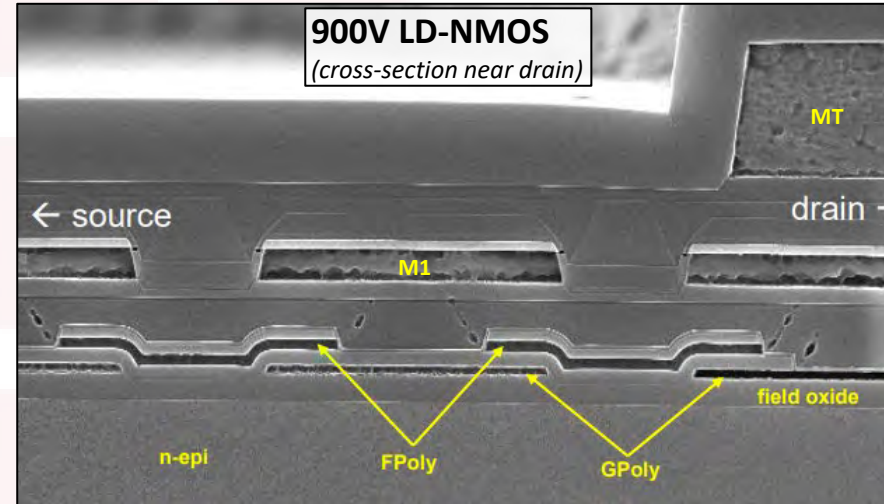


- SG5HV is a 20 layer high voltage (900V) BCD technology with deep trench isolation and 2LM.

Item	SG5HV
Design rules	0.35um
Process	3BL-EPI 2P/2M
Mask count	20L
Epi	7.0um, 4.57ohm-cm
GOX	600A
CMOS	NMOS: 1.4um PMOS: 1.4um
Isolation	LOCOS / Deep Trench / JI
Silicidation	CoSi
M1 (Tk)	0.5um
MT (Tk)	2.0um
CMOS	7V/20V
Bipolar	15V/30V/40V
Diode	6V
Capacitor	PI-Poly, Poly-Top metal
Resistor	2.5Kohm/sq
LDMOS	900V



Layer name.	Layer description
LN	N-type lightly doped buried well
NB	N-type buried layer
PB	P-type buried layer
TR	Deep trench
PI	P-isolation diffusion
PW	HV Pwell
DE	Device, Active
PV	Vt implant block
RP	N+ Poly doping
GP	Gate polysilicon
NLD	N-MOS LDD
NP	N+ S/D
PP	P+ S/D
FP	Field polysilicon
SB	Salicide Block
CT	Contact
M1	Metal1
V1	Via1
MT	Top metal
PA	Passivation open